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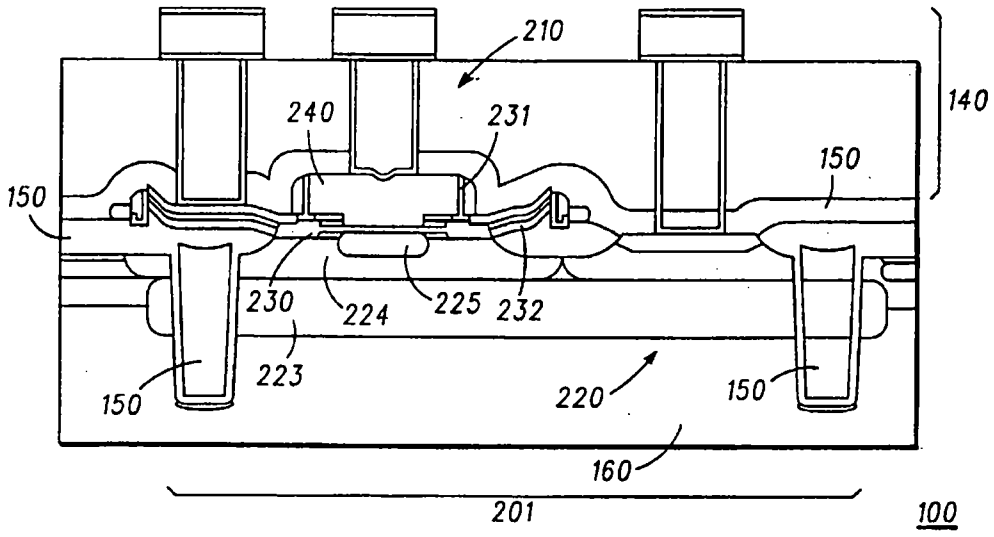
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[Continued on next page]

(54) Title: METHOD OF MANUFACTURING A HETEROJUNCTION BICMOS INTEGRATED CIRCUIT



(57) Abstract: A method of manufacturing a heterojunction BiCMOS IC (100) includes forming a gate electrode (121, 131), forming a protective layer (901, 902) over the gate electrode, forming a semiconductor layer (1101) over the protective layer, depositing an electrically insulative layer (1102, 1103) over the semiconductor layer, using a mask layer (1104) to define a doped region (225) in the semiconductor layer and to define a hole (1201) in the electrically insulative layer, forming an electrically conductive layer (1301) over the electrically insulative layer, using another mask layer (1302) to define an emitter region (240) in the electrically conductive layer and to define an intrinsic base region (231) and a portion of an extrinsic base region (1502) to define another portion of the extrinsic base region in the electrically conductive layer.

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